

## List of Publications by Citations

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

16  
papers

3,982  
citations

12  
h-index

16  
g-index

16  
ext. papers

4,433  
ext. citations

11  
avg, IF

4.89  
L-index

#	Paper	IF	Citations
16	Integrated circuits based on bilayer MoS <sub>2</sub> transistors. <i>Nano Letters</i> , <b>2012</b> , 12, 4674-80	11.5	1350
15	Role of the seeding promoter in MoS <sub>2</sub> growth by chemical vapor deposition. <i>Nano Letters</i> , <b>2014</b> , 14, 464-472	11.5	534
14	Synthesis and transfer of single-layer transition metal disulfides on diverse surfaces. <i>Nano Letters</i> , <b>2013</b> , 13, 1852-7	11.5	524
13	Graphene/MoS <sub>2</sub> hybrid technology for large-scale two-dimensional electronics. <i>Nano Letters</i> , <b>2014</b> , 14, 3055-63	11.5	472
12	Dielectric screening of excitons and trions in single-layer MoS <sub>2</sub> . <i>Nano Letters</i> , <b>2014</b> , 14, 5569-76	11.5	399
11	High-Performance WSe <sub>2</sub> Complementary Metal Oxide Semiconductor Technology and Integrated Circuits. <i>Nano Letters</i> , <b>2015</b> , 15, 4928-34	11.5	163
10	Parallel Stitching of 2D Materials. <i>Advanced Materials</i> , <b>2016</b> , 28, 2322-9	24	161
9	Origin and Control of OFF-State Leakage Current in GaN-on-Si Vertical Diodes. <i>IEEE Transactions on Electron Devices</i> , <b>2015</b> , 62, 2155-2161	2.9	122
8	Design, Modeling, and Fabrication of Chemical Vapor Deposition Grown MoS Circuits with E-Mode FETs for Large-Area Electronics. <i>Nano Letters</i> , <b>2016</b> , 16, 6349-6356	11.5	102
7	High-Risk Breast Lesions: A Machine Learning Model to Predict Pathologic Upgrade and Reduce Unnecessary Surgical Excision. <i>Radiology</i> , <b>2018</b> , 286, 810-818	20.5	86
6	Large-Area 2-D Electronics: Materials, Technology, and Devices. <i>Proceedings of the IEEE</i> , <b>2013</b> , 101, 1638-1652	14.52	39
5	Topological insulator nanostructures: Materials synthesis, Raman spectroscopy, and transport properties. <i>Frontiers of Physics</i> , <b>2012</b> , 7, 208-217	3.7	17
4	Negative rectification and negative differential resistance in nanoscale single-walled carbon nanotube p-n junctions. <i>Theoretical Chemistry Accounts</i> , <b>2011</b> , 130, 353-359	1.9	9
3	Heterogeneous Integration of 2D Materials and Devices on a Si Platform <b>2019</b> , 43-84		2
2	MoS <sub>2</sub> FET fabrication and modeling for large-scale flexible electronics <b>2015</b> ,		1
1	Two-dimensional materials for ubiquitous electronics <b>2013</b> ,		1